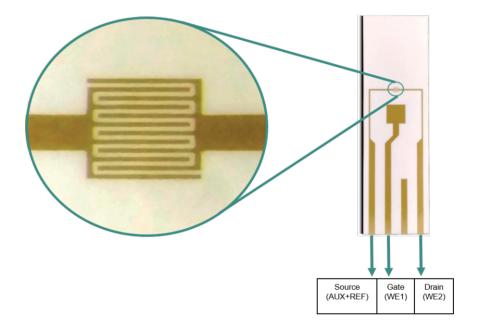
Flexible Gold Field-Effect Transistors with coplanar gate

∩1 Ref. AUFET30

Disposable flexible devices for Field-Effect Transistor (FET) are made of gold onto plastic substrate. These electrodes are useful to obtain sensing phases. The interdigitated area (drain and source) should be modified with a semiconductor. The gate modification is optional for different purposes. The current circulated between the drain and source is the parameter under study that varies depending of the WEs modifications.

The coplanar design of this integrated device facilitates its use and reduces the sample required for the experiment.



Plastic substrate: L34 x W10 x H0.175 mm

Electric contacts: Gold

The AUFET30 electrode consists on:

 $\textit{Drain-Source Channel:} \ \ \text{Gold interdigitated electrodes with 30 } \mu \text{m} \ \ \text{band/gap dimensions}$

Gate: 3×3 mm square gold electrode

AUFET30 electrodes are commercialized in 50 units per pack. Specific connector ref. BIDSC-FET connects the electrode to the potentiostat. The sensors should be stored at room temperature in a dry place.

www.metrohm-dropsens.com

